MOSFET - Power, Single N-Channel, SO-8FL

30 V, 52 A

NTMFS4C08N

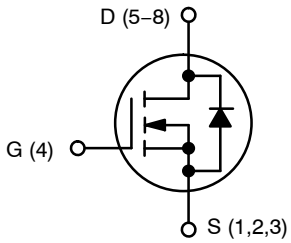
$V_{(BR)DSS}$	$R_{DS(ON)}$ MAX	I_D MAX
30 V	5.8 mΩ @ 10 V	52 A
	8.5 mΩ @ 4.5 V	

Features

- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Capacitance to Minimize Driver Losses
- Optimized Gate Charge to Minimize Switching Losses
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- CPU Power Delivery
- DC−DC Converters



N−CHANNEL MOSFET

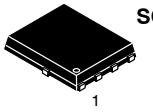
MAXIMUM RATINGS (T_J = 25°C unless otherwise stated)

Parameter			Symbol	Value	Unit
Drain−to−Source Voltage			V_{DSS}	30	V
Gate−to−Source Voltage			V_{GS}	±20	V
Continuous Drain Current $R_{\theta JA}$ (Note 2)	Steady State	T_A = 25°C	I_D	16.4	A
		T_A = 80°C		12.3	
Power Dissipation $R_{\theta JA}$ (Note 2)		T_A = 25°C	P_D	2.51	W
Continuous Drain Current $R_{\theta JA} \le 10$ s (Note 2)		T_A = 25°C	I_D	25.3	A
		T_A = 80°C		19.0	
Power Dissipation $R_{\theta JA} \le 10$ s (Note 2)		T_A = 25°C	P_D	6.0	W
Continuous Drain Current $R_{\theta JA}$ (Note 3)		T_A = 25°C	I_D	9.0	A
		T_A = 80°C		6.8	
Power Dissipation $R_{\theta JA}$ (Note 3)		T_A = 25°C	P_D	0.76	W
Continuous Drain Current $R_{\theta JC}$ (Note 2)		T_C = 25°C	I_D	52	A
		T_C =80°C		39	
Power Dissipation $R_{\theta JC}$ (Note 2)		T_C = 25°C	P_D	25.5	W
Pulsed Drain Current	T_A = 25°C, t_p = 10 μs		I_{DM}	144	A
Pulsed Source Current (Body Diode)	T_A = 25°C, t_p = 10 μs		I_{SM}	560	A
Current Limited by Package		T_A = 25°C	I_{Dmax}	80	A
Operating Junction and Storage Temperature Range			T_J, T_{STG}	−55 to +150	°C
Source Current (Body Diode)			I_S	23	A
Drain to Source DV/DT			dV/d_t	7.0	V/ns
Single Pulse Drain−to−Source Avalanche Energy (T_J = 25°C, V_{GS} = 10 V, I_L = 29 A_{pk}, L = 0.1 mH, R_{GS} = 25 Ω) (Note 4)			E_{AS}	42	mJ
Lead Temperature for Soldering Purposes (1/8″ from case for 10 s)			T_L	260	°C

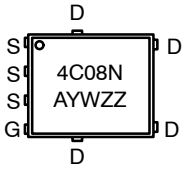
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

2. Surface−mounted on FR4 board using 1 sq−in pad, 1 oz Cu.
3. Surface−mounted on FR4 board using the minimum recommended pad size.
4. This is the absolute maximum rating. Parts are 100% tested at T_J = 25°C, V_{GS} = 10 V, I_L = 21 Apk, E_{AS} = 22 mJ.

MARKING DIAGRAM



SO−8 FLAT LEAD
CASE 488AA
STYLE 1



A = Assembly Location
Y = Year
W = Work Week
ZZ = Lot Traceabililty

ORDERING INFORMATION

Device	Package	Shipping†
NTMFS4C08NT1G	SO−8 FL (Pb−Free)	1500 / Tape & Reel

DISCONTINUED (Note 1)

NTMFS4C08NT3G	SO−8 FL (Pb−Free)	5000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

1. **DISCONTINUED:** This device is not recommended for new design. Please contact your **onsemi** representative for information. The most current information on this device may be available on www.onsemi.com.

© Semiconductor Components Industries, LLC, 2012

THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction−to−Case (Drain)	$R_{\theta JC}$	4.9	°C/W
Junction−to−Ambient − Steady State (Note 5)	$R_{\theta JA}$	49.8	
Junction−to−Ambient − Steady State (Note 6)	$R_{\theta JA}$	164.6	
Junction−to−Ambient − (t ≤ 10 s) (Note 5)	$R_{\theta JA}$	21.0	

5. Surface−mounted on FR4 board using 1 sq−in pad, 1 oz Cu.
6. Surface−mounted on FR4 board using the minimum recommended pad size.

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition		Min	Typ	Max	Unit
OFF CHARACTERISTICS							
Drain−to−Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = 250 μA		30			V
Drain−to−Source Breakdown Voltage (transient)	$V_{(BR)DSSt}$	V_{GS} = 0 V, $I_{D(aval)}$ = 8.4 A, T_{case} = 25°C, $t_{transient}$ = 100 ns		34			V
Drain−to−Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}$/T_J				13.8		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	V_{GS} = 0 V, V_{DS} = 24 V	T_J = 25°C			1.0	μA
			T_J = 125°C			10	
Gate−to−Source Leakage Current	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±20 V				±100	nA
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	$V_{GS(TH)}$	V_{GS} = V_{DS}, I_D = 250 μA		1.3		2.1	V
Negative Threshold Temperature Coefficient	$V_{GS(TH)}$/T_J				4.9		mV/°C
Drain−to−Source On Resistance	$R_{DS(on)}$	V_{GS} = 10 V	I_D = 18 A		4.6	5.8	mΩ
		V_{GS} = 4.5 V	I_D = 30 A		6.8	8.5	
Forward Transconductance	g_{FS}	V_{DS} = 1.5 V, I_D = 15 A			42		S
Gate Resistance	R_G	T_A = 25°C		0.3	1.0	2.0	Ω
CHARGES AND CAPACITANCES							
Input Capacitance	C_{ISS}	V_{GS} = 0 V, f = 1 MHz, V_{DS} = 15 V			1113	1670	pF
Output Capacitance	C_{OSS}				702		
Reverse Transfer Capacitance	C_{RSS}				39		
Capacitance Ratio	C_{RSS}/C_{ISS}	V_{GS} = 0 V, V_{DS} = 15 V, f = 1 MHz			0.035		
Total Gate Charge	$Q_{G(TOT)}$	V_{GS} = 4.5 V, V_{DS} = 15 V; I_D = 30 A			8.4		nC
Threshold Gate Charge	$Q_{G(TH)}$				1.8		
Gate−to−Source Charge	Q_{GS}				3.5		
Gate−to−Drain Charge	Q_{GD}				3.3		
Gate Plateau Voltage	V_{GP}				3.4		V
Total Gate Charge	$Q_{G(TOT)}$	V_{GS} = 10 V, V_{DS} = 15 V; I_D = 30 A			18.2		nC
SWITCHING CHARACTERISTICS (Note 8)							
Turn−On Delay Time	$t_{d(ON)}$	V_{GS} = 4.5 V, V_{DS} = 15 V, I_D = 15 A, R_G = 3.0 Ω			9.0		ns
Rise Time	t_r				33		
Turn−Off Delay Time	$t_{d(OFF)}$				15		
Fall Time	t_f				4.0		

7. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.
8. Switching characteristics are independent of operating junction temperatures.

Share Feedback
Your Opinion Matters

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition		Min	Typ	Max	Unit
SWITCHING CHARACTERISTICS (Note 8)							
Turn−On Delay Time	$t_{d(ON)}$	V_{GS} = 10 V, V_{DS} = 15 V, I_D = 15 A, R_G = 3.0 Ω			7.0		ns
Rise Time	t_r				26		
Turn−Off Delay Time	$t_{d(OFF)}$				19		
Fall Time	t_f				3.0		
DRAIN−SOURCE DIODE CHARACTERISTICS							
Forward Diode Voltage	V_{SD}	V_{GS} = 0 V, I_S = 10 A	T_J = 25°C		0.79	1.1	V
			T_J = 125°C		0.66		
Reverse Recovery Time	t_{RR}	V_{GS} = 0 V, dIS/dt = 100 A/μs, I_S = 30 A			28.3		ns
Charge Time	t_a				14.5		
Discharge Time	t_b				13.8		
Reverse Recovery Charge	Q_{RR}				15.3		nC

7. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.
8. Switching characteristics are independent of operating junction temperatures.

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

Share Feedback
Your Opinion Matters

TYPICAL CHARACTERISTICS

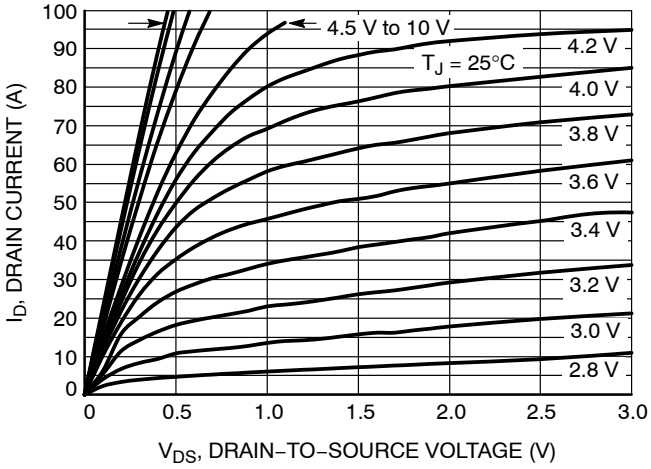


Figure 1. On−Region Characteristics

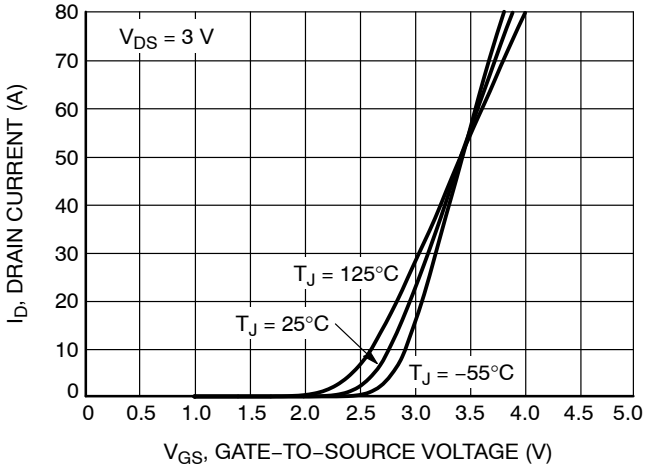


Figure 2. Transfer Characteristics

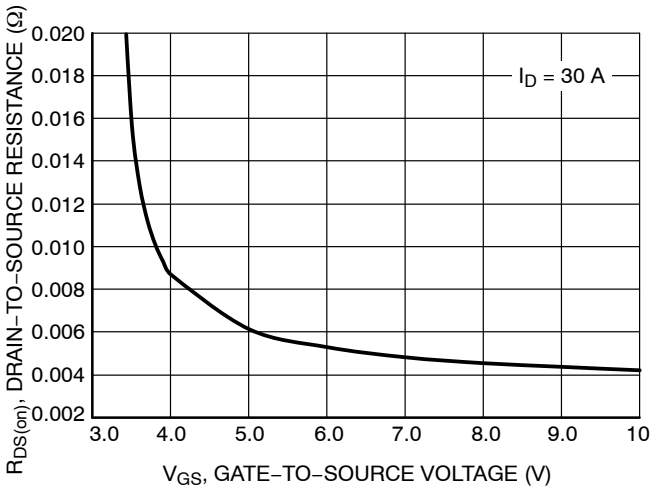


Figure 3. On−Resistance vs. V_{GS}

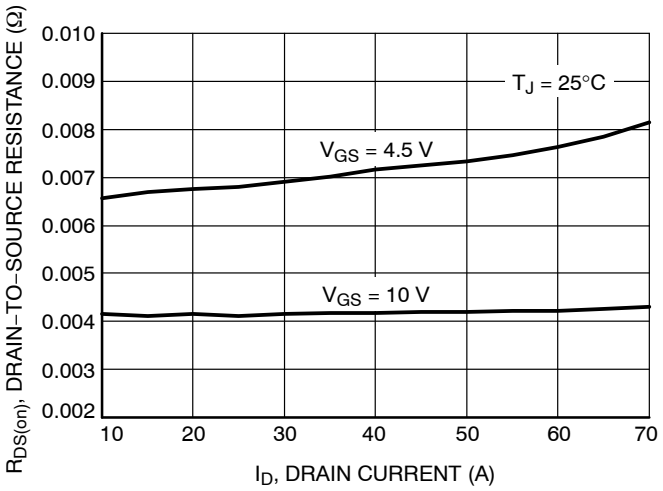


Figure 4. On−Resistance vs. Drain Current and Gate Voltage

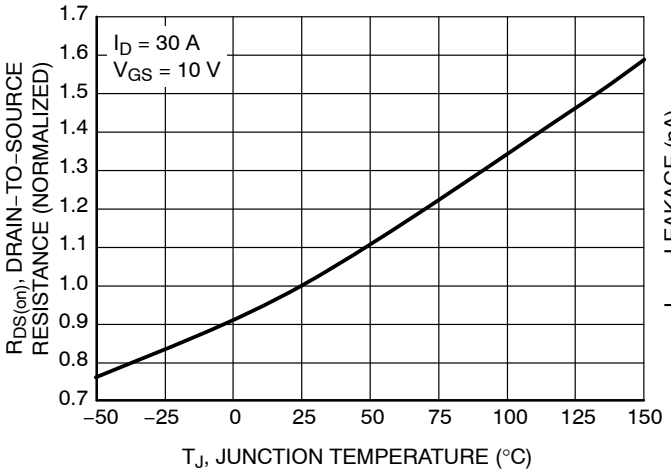


Figure 5. On−Resistance Variation with Temperature

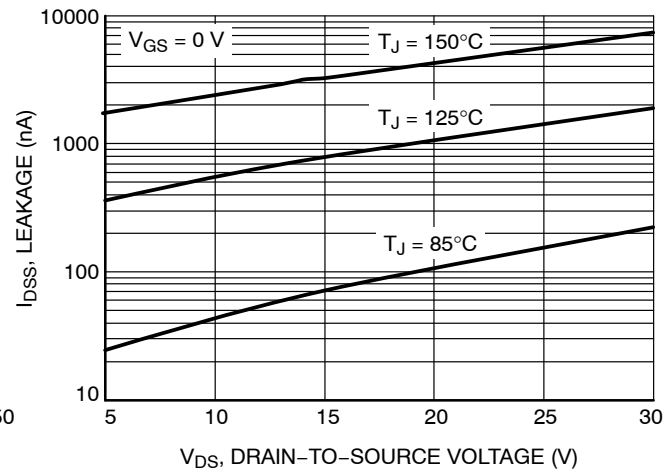


Figure 6. Drain−to−Source Leakage Current vs. Voltage

Share Feedback
Your Opinion Matters

TYPICAL CHARACTERISTICS

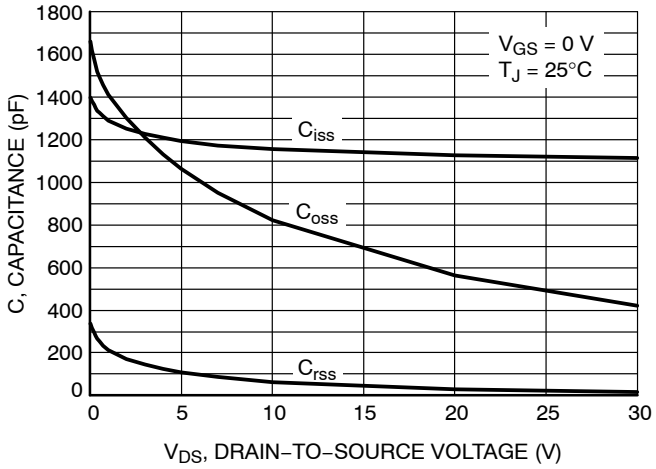


Figure 7. Capacitance Variation

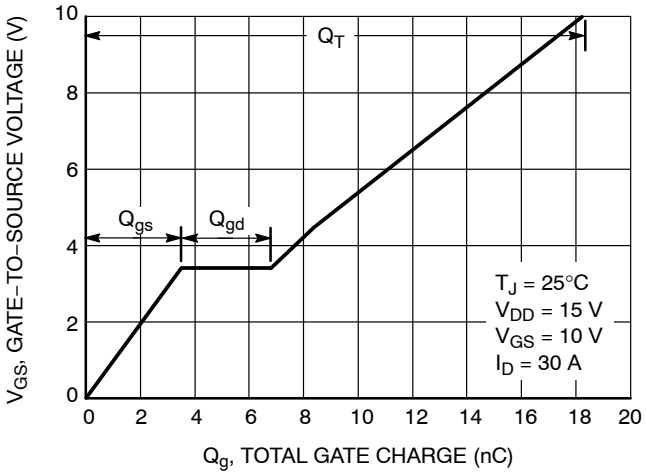


Figure 8. Gate−to−Source and Drain−to−Source Voltage vs. Total Charge

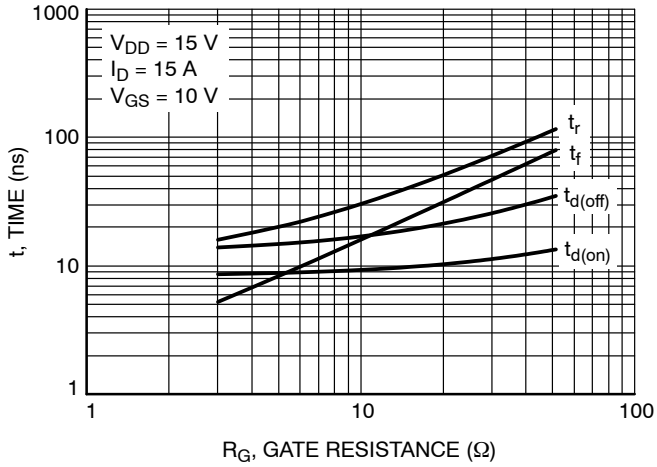


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

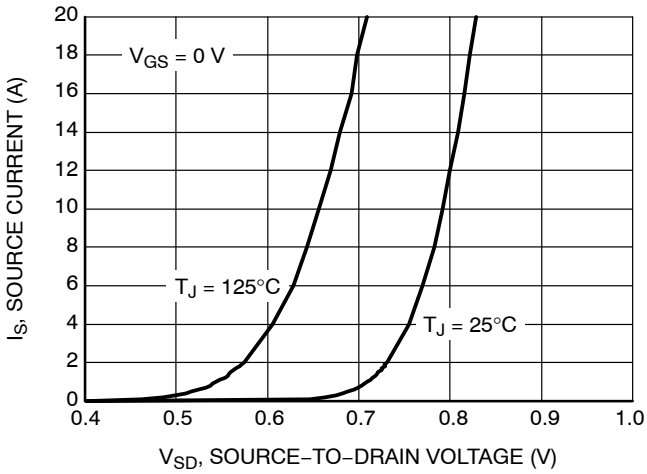


Figure 10. Diode Forward Voltage vs. Current

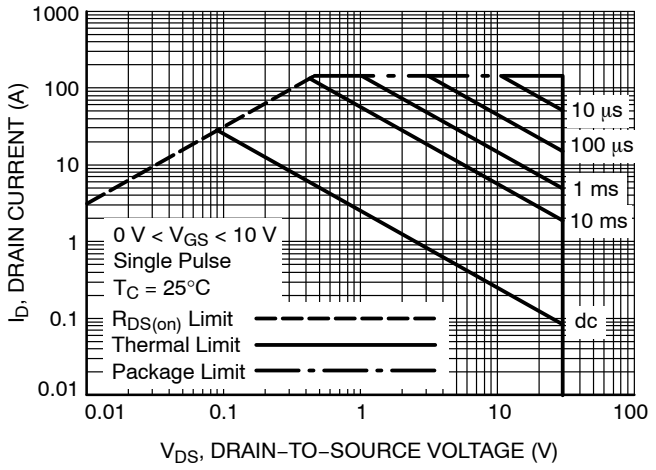


Figure 11. Maximum Rated Forward Biased Safe Operating Area

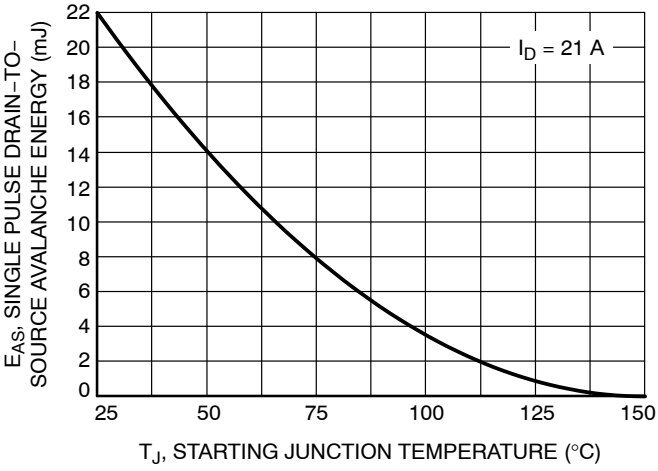


Figure 12. Maximum Avalanche Energy vs. Starting Junction Temperature

Share Feedback
Your Opinion Matters

TYPICAL CHARACTERISTICS

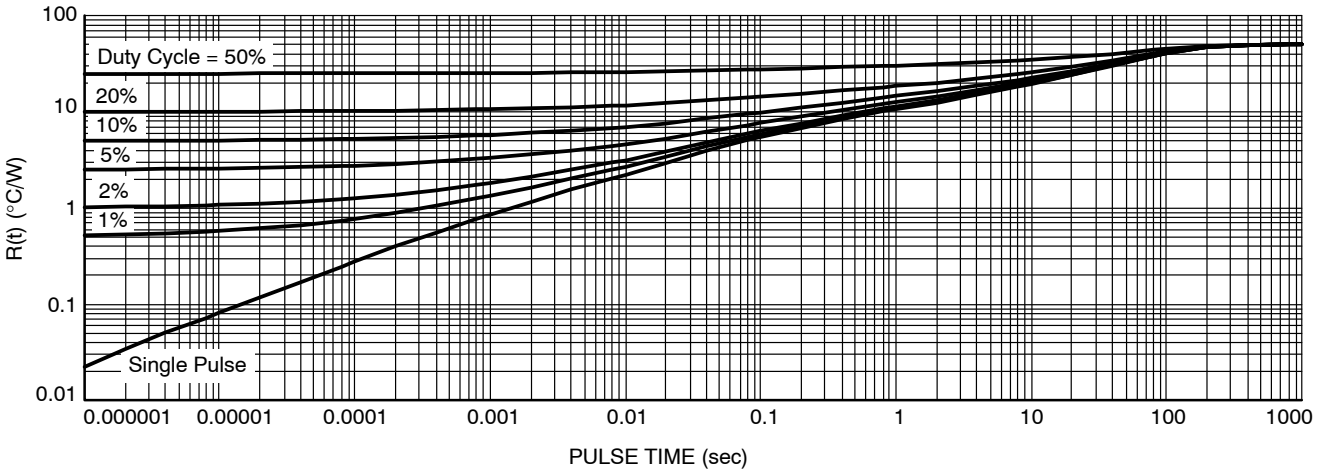


Figure 13. Thermal Response

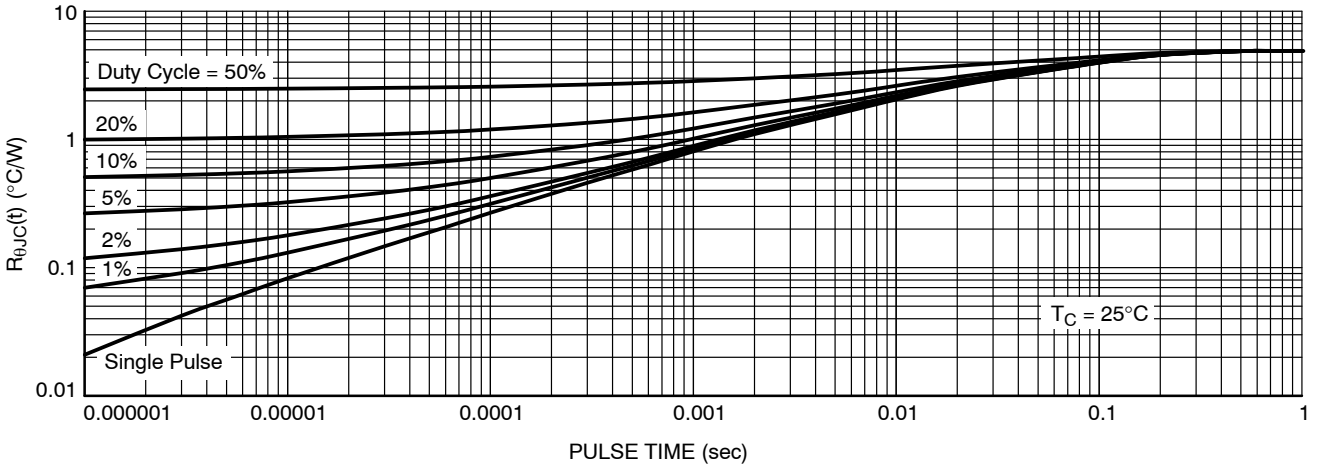


Figure 14. Thermal Response

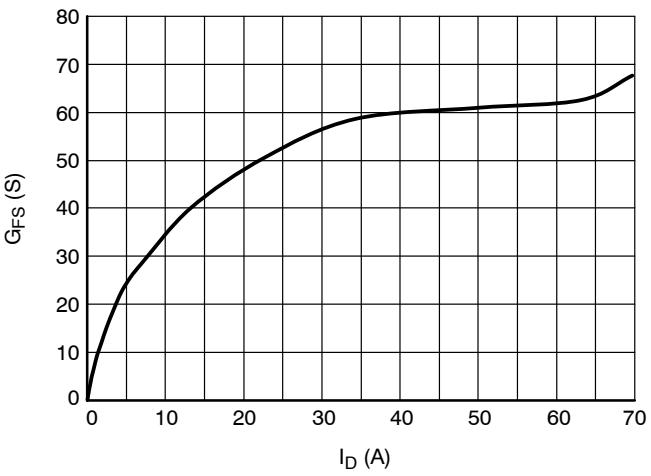


Figure 15. G_{FS} vs. I_D

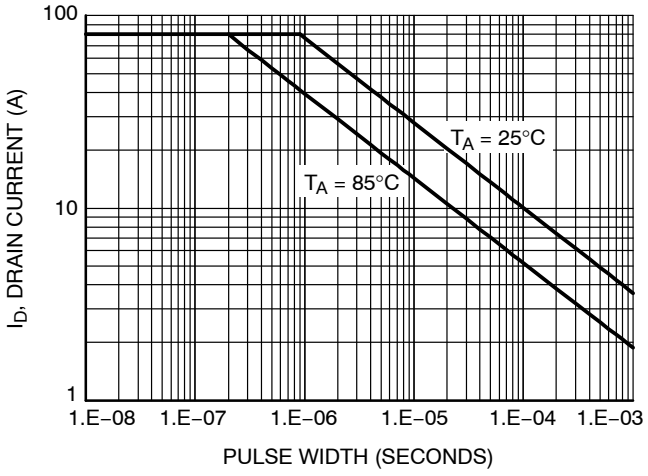
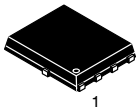


Figure 16. Avalanche Characteristics

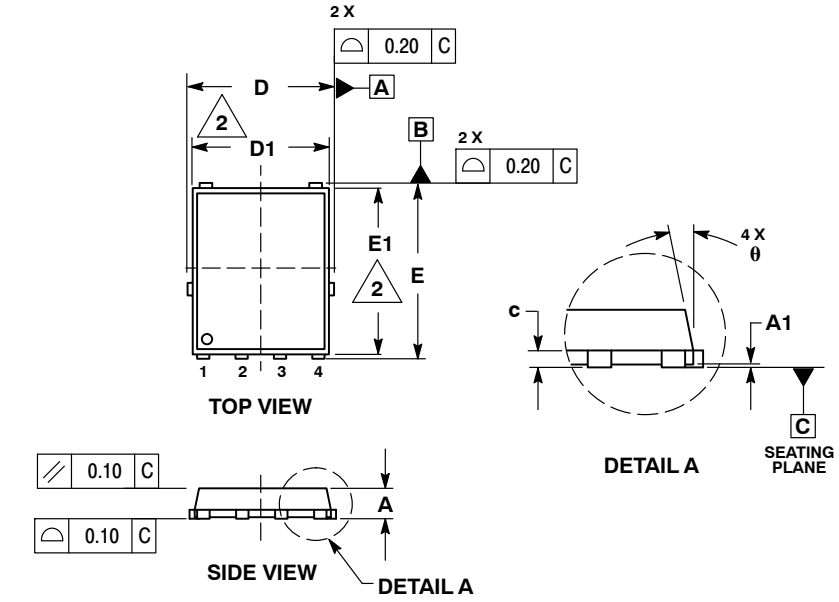
Share Feedback
Your Opinion Matters



SCALE 2:1

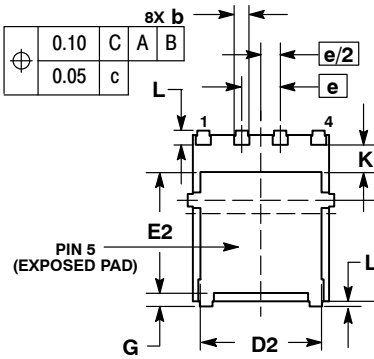
DFN5 5x6, 1.27P
(SO−8FL)
CASE 488AA
ISSUE N

DATE 25 JUN 2018

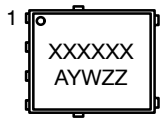


NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION D1 AND E1 DO NOT INCLUDE MOLD FLASH PROTRUSIONS OR GATE BURRS.

	MILLIMETERS		
DIM	MIN	NOM	MAX
A	0.90	1.00	1.10
A1	0.00	–––	0.05
b	0.33	0.41	0.51
c	0.23	0.28	0.33
D	5.00	5.15	5.30
D1	4.70	4.90	5.10
D2	3.80	4.00	4.20
E	6.00	6.15	6.30
E1	5.70	5.90	6.10
E2	3.45	3.65	3.85
e	1.27 BSC		
G	0.51	0.575	0.71
K	1.20	1.35	1.50
L	0.51	0.575	0.71
L1	0.125 REF		
M	3.00	3.40	3.80
θ	0 °	–––	12 °



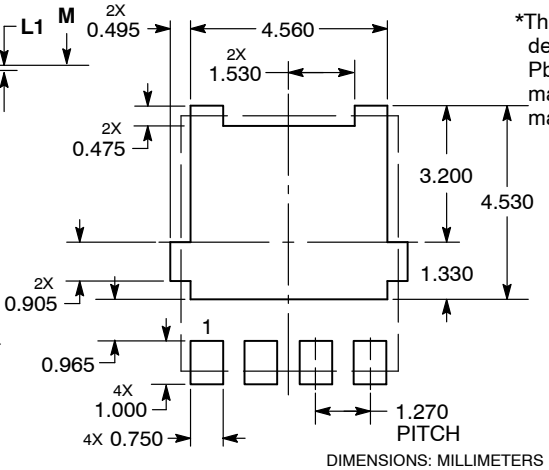
GENERIC MARKING DIAGRAM*



XXXXXX = Specific Device Code
A = Assembly Location
Y = Year
W = Work Week
ZZ = Lot Traceability

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “ ▪”, may or may not be present. Some products may not follow the Generic Marking.

RECOMMENDED SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

STYLE 1:
PIN 1. SOURCE
2. SOURCE
3. SOURCE
4. GATE
5. DRAIN

STYLE 2:
PIN 1. ANODE
2. ANODE
3. ANODE
4. NO CONNECT
5. CATHODE

*For additional information on our Pb−Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

DOCUMENT NUMBER:	**98AON14036D**	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped “CONTROLLED COPY” in red.	
DESCRIPTION:	**DFN5 5x6, 1.27P (SO−8FL)**		**PAGE 1 OF 1**

onsemi and onsemi are trademarks of Semiconductor Components Industries, LLC dba **onsemi** or its subsidiaries in the United States and/or other countries. **onsemi** reserves the right to make changes without further notice to any products herein. **onsemi** makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. **onsemi** does not convey any license under its patent rights nor the rights of others.

onsemi, ONSEMI , and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi**'s product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent−Marking.pdf. **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as−is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:
Technical Library: www.onsemi.com/design/resources/technical−documentation
onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support
For additional information, please contact your local Sales Representative at
www.onsemi.com/support/sales